

Phase Noise in LC Oscillators

Konstantin A. Kouznetsov and Robert G. Meyer

Abstract—Analytical methods for the phase-noise analysis of LC -tuned oscillators are presented. The fundamental assumption used in the theoretical model is that an oscillator acts as a large-signal LC -tuned amplifier for purposes of noise analysis. This approach allows us to derive closed-form expressions for the close-to-carrier spectral density of the output noise, and to estimate the phase-noise performance of an oscillator from circuit parameters using hand analysis. The emphasis is on an engineering approach intended to facilitate rapid estimation of oscillator phase noise. Theoretical predictions are compared with results of circuit simulations using a nonlinear phase-noise simulator. The analytical results are in good agreement with simulations for weakly nonlinear oscillators. Complete nonlinear simulations are necessary to accurately predict phase noise in oscillators operating in a strongly nonlinear regime. To confirm the validity of the nonlinear phase-noise models implemented in the simulator, simulation results are compared with measurements of phase noise in a practical Colpitts oscillator, where we find good agreement between simulations and measurements.

Index Terms—Jitter, noise, oscillator, phase noise, voltage-controlled oscillator.

I. INTRODUCTION

VOLTAGE-CONTROLLED oscillators (VCO's) are essential building blocks of wireless communication systems, where the spectral quality of the local oscillator signal directly influences the out-of-band interference. Phase noise in oscillators has long been the subject of theoretical and experimental investigation. An early model of phase noise, introduced by Leeson [1], qualitatively described phase-noise spectra in a variety of oscillators. Theoretical derivations of the Leeson formula rely mostly on a linear time-invariant approach to the analysis of noise in oscillators [2]–[4]. Treatments of nonlinear effects on oscillator noise have also been developed [5], [6]. Recently, general theories that allow quantitative predictions of phase noise have been introduced [7]–[9]. These exact approaches naturally lend themselves to computer-aided analysis. A complete nonlinear phase-noise simulator that utilizes approaches similar to those of [7]–[9] has been implemented in a commercial simulation package [10].

In this paper, we explore the validity and limitations of linear noise analysis of LC -tuned oscillators. We examine and exploit the assumption that an LC feedback oscillator acts as a high-gain, large-signal LC amplifier with respect to its noise sources

Manuscript received November 23, 1999; revised April 19, 2000. This work was supported by the Army Research Office under Grant DAAG55-97-1-0340.

K. A. Kouznetsov was with the Department of Electrical Engineering and Computer Science, University of California, Berkeley, CA 94720-1772 USA. He is now with Maxim Integrated Products, Sunnyvale, CA 94086 USA (e-mail: kouznets@mxim.com).

R. G. Meyer is with the Department of Electrical Engineering and Computer Science, University of California, Berkeley, CA 94720-1772 USA.

Publisher Item Identifier S 0018-9200(00)06439-8.

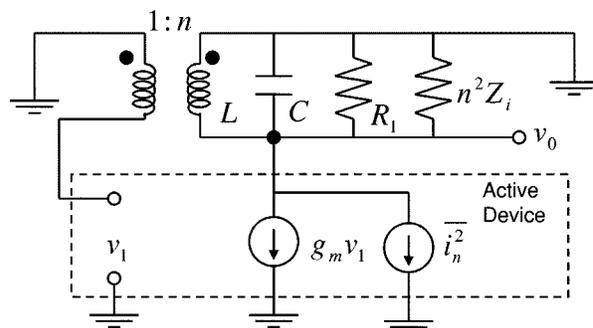


Fig. 1. AC schematic diagram of an LC -tuned transformer-coupled oscillator showing a single current noise source referred to the output of the active device.

despite the nonlinear limiting that occurs in steady-state oscillation. This approach allows us to make quantitative estimates of the phase-noise performance of LC oscillators with a weak nonlinearity, giving predictions which are in good agreement with nonlinear simulations with the SpectreRF simulator. Our engineering techniques provide insights and quantitative understanding of noise in oscillators and serve as a starting point in a design procedure for practical oscillators that should include complete nonlinear simulations.

II. OSCILLATOR NOISE THEORY

In the analysis of phase noise of an LC oscillator, we assume that an oscillator is operating in the steady state at a fundamental frequency f_0 and only wide-sense stationary noise sources are superimposed onto the oscillating waveform. In a nonlinear system noise sidebands at frequencies $kf_0 \pm \delta f$ also contribute to output noise at close-to-carrier frequencies $f_0 \pm \delta f$ via processes of nonlinear mixing; here, k is an integer between $+\infty$ and $-\infty$. For clarity of the discussion that follows, we derive the phase noise of the oscillator at the output frequency $f_0 - \delta f$. We further assume that the oscillator is operating in a near-linear fashion such that noise sidebands close to the carrier provide the dominant contribution to oscillator noise and mixing from other harmonics is suppressed.

Without loss of generality, the circuit diagram of an LC -tuned oscillator can be represented as shown in Fig. 1 [11]. The loop gain is assumed to be just less than unity, so that the circuit behaves as a high-gain LC positive-feedback amplifier. As the oscillation amplitude builds up, the influence of the negative resistance provided by the active device is reduced (due to soft limiting or AGC action) such that in the steady state, the output spectrum of an oscillator contains a very sharp noise peak at its fundamental frequency, resulting from the oscillator limiting on its own amplified noise.

To determine the noise transfer function from the noise generator i_n^2 to the oscillator output, we consider effects of noise

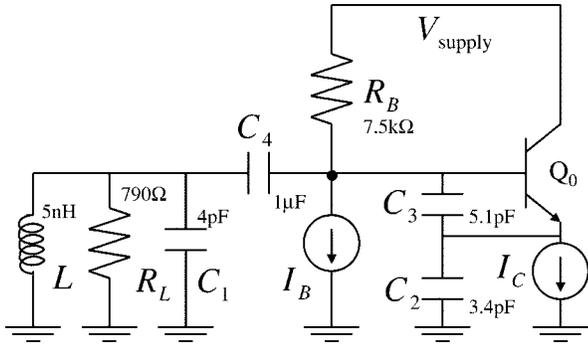


Fig. 2. Circuit diagram of a Colpitts oscillator with the collector of Q_0 ac grounded.

modulation to positive and negative sidebands. As we show in the Appendix, the noise power at $f_0 - \delta f$ will be equally distributed between sidebands at $f_0 - \delta f$ and $-f_0 - \delta f$ leading to the noise transfer function α_0 at $f_0 - \delta f$, which can be written as

$$\alpha_0 = \frac{1}{2} \times \frac{R_L}{2jQ} \left(\frac{f_0}{\delta f} \right). \quad (1)$$

This expression explicitly contains a factor of 1/2 resulting from noise spreading to positive and negative frequencies. Similarly, a noise tone at $-f_0 - \delta f$, which is uncorrelated with the tone at $f_0 - \delta f$, is spread evenly between $-f_0 - \delta f$ and $f_0 - \delta f$ in the output noise spectrum. To determine the total noise at the output at $f_0 - \delta f$, contributions from positive and negative frequencies must be added in quadrature leading to the total noise spectral density at $f_0 - \delta f$, \bar{v}_t^2 , given by

$$\bar{v}_t^2 = 2 \times \bar{i}_n^2 \times \frac{1}{4} \times \frac{R_L^2}{4Q^2} \left(\frac{f_0}{\delta f} \right)^2. \quad (2)$$

We note that the total output noise of an LC oscillator given by (2) is 1/2 of the noise power of an LC tank with the same Q . This distinction in the noise shaping between an oscillator and a resonant circuit has been pointed out previously in [10].

It is frequently stated that close-to-carrier oscillator noise can be decomposed into AM- and PM-modulated parts with the AM-modulated part being suppressed due to amplitude limiting in the steady state of oscillation. This reasoning often leads to the inclusion of a factor of 1/2 into phase-noise expressions. We perform our calculations in a manner which is similar to the noise analysis of a positive-feedback amplifier, and do not include an additional factor of 1/2 in derivations. Therefore, we use the terms oscillator noise and phase noise interchangeably, meaning total noise at the oscillator output.

III. COLPITTS OSCILLATOR ANALYSIS

To test the validity of our approach to the noise analysis of LC oscillators, we analyze phase noise in a Colpitts oscillator. A circuit diagram of a Colpitts oscillator with the collector of the active device ac grounded is shown in Fig. 2. The active device is a bipolar-junction transistor Q_0 biased by dc current sources I_C and I_B , and resistor R_B . The capacitive transformer formed by capacitors C_2 and C_3 provides the positive feedback

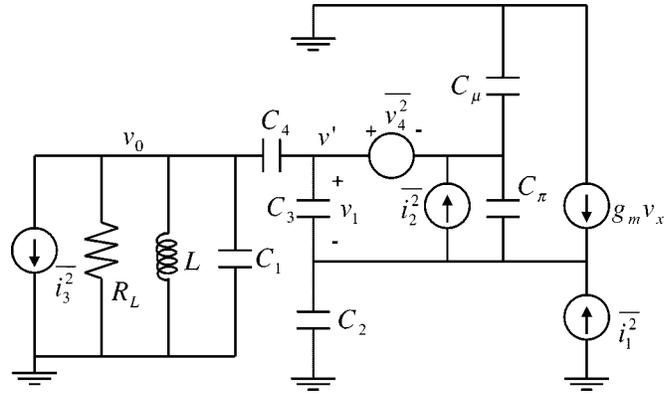


Fig. 3. Small-signal model of the Colpitts oscillator used for the phase noise analysis.

needed to induce oscillation. The coupling capacitor C_4 can be chosen to provide additional transformations from the base of Q_0 to the tank circuit, or a large value of C_4 can be chosen to provide a short circuit between the base of Q_0 and the tank at the oscillation frequency.

We consider the Colpitts oscillator biased at a relatively low value of the collector bias current, $I_C = 0.2$ mA. This value is chosen to set the initial loop gain at 1.5, which is sufficiently close to unity to create a weakly nonlinear oscillator. The small-signal ac circuit used for the noise analysis is shown in Fig. 3. Four noise sources are included in the analysis: collector-current shot noise i_1 , base-current shot noise i_2 , thermal-current noise in the tank resistance i_3 produced by the resistance $R_L = 790 \Omega$, and thermal voltage noise in base resistance v_4 produced by the resistance $r_b = 7.6 \Omega$. Circuit parasitics have not been included for clarity of comparison of analytical results and simulations.

Solving circuit equations, we derive transfer functions from a particular noise source to the output at the frequency $f_0 - \delta f$ in a manner identical to derivations presented in the Appendix. For low values of the collector bias current, the assumption of small g_m , i.e., $g_m \ll |sC_2|, |sC_3|$, is valid, in which case, noise transfer functions are found as follows:

$$\alpha_0^{(1)} = \frac{1}{2} \times \frac{C_3}{C_2 + C_3} \times \frac{1}{2j\omega_0 C_{\text{eff}}} \left(\frac{f_0}{\delta f} \right) \quad (3)$$

$$\alpha_0^{(2)} = \frac{1}{2} \times \frac{C_2}{C_2 + C_3} \times \frac{1}{2j\omega_0 C_{\text{eff}}} \left(\frac{f_0}{\delta f} \right) \quad (4)$$

$$\alpha_0^{(3)} = \frac{1}{2} \times \frac{1}{2j\omega_0 C_{\text{eff}}} \left(\frac{f_0}{\delta f} \right) \quad (5)$$

$$\alpha_0^{(4)} = \frac{1}{2} \times \frac{C_2 + C_3}{C_2} \times \frac{1}{2jQ} \left(\frac{f_0}{\delta f} \right) \quad (6)$$

where $\alpha_0^{(1)}$, $\alpha_0^{(2)}$, $\alpha_0^{(3)}$, and $\alpha_0^{(4)}$ refer to noise sources i_1 , i_2 , i_3 , and v_4 , respectively, $C_{\text{eff}} = C_1 + C_2 C_3 / (C_2 + C_3)$ is the effective tank capacitance, and Q is the loaded quality factor of the tank. The phase noise contribution due to the k th noise source is determined by multiplying its noise spectral density by the square of the appropriate transfer function, as follows:

$$PN_0^{(k)} = N_k \left(\alpha_0^{(k)} \right)^2 \quad (7)$$

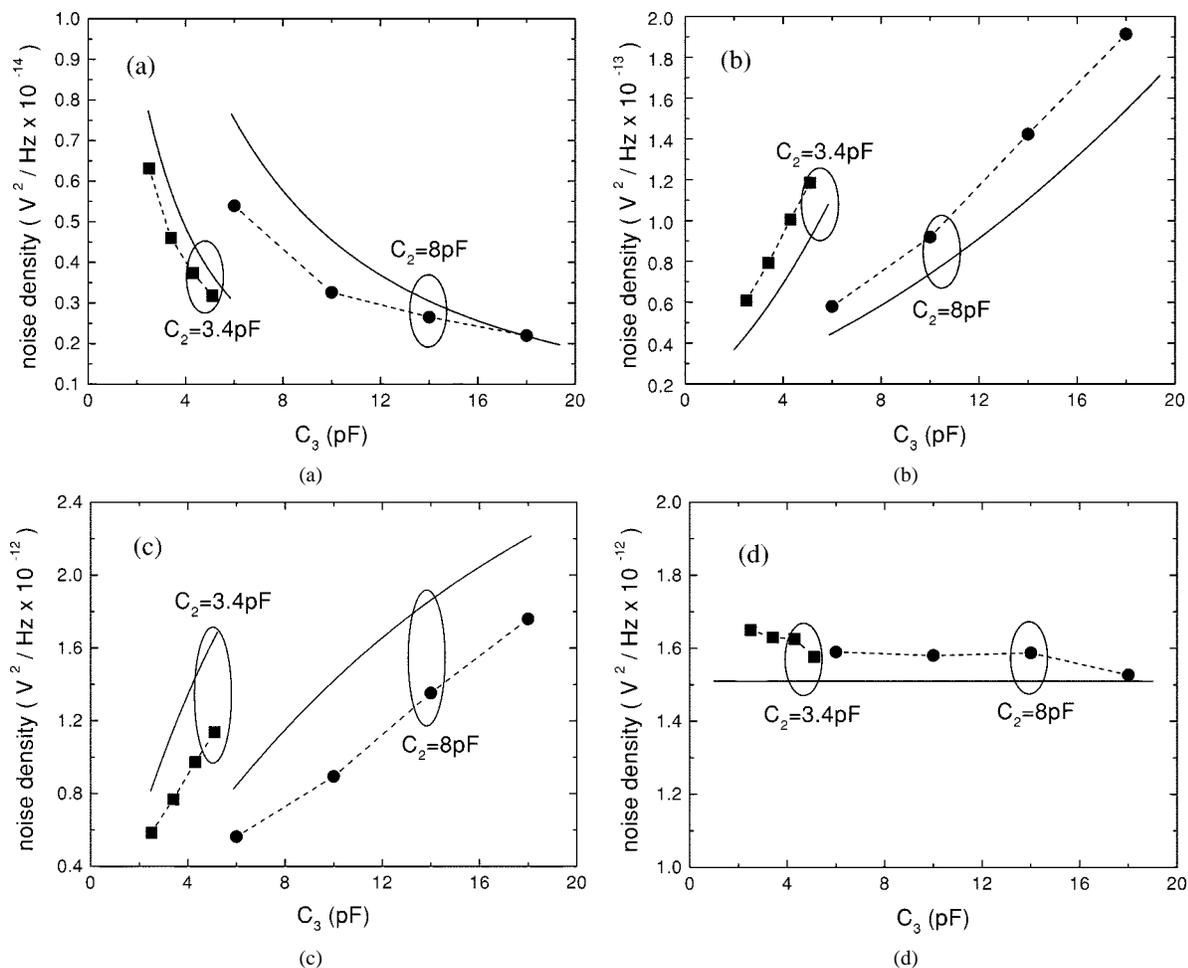


Fig. 4. Simulation results of a weakly nonlinear Colpitts oscillator for $C_2 = 3.4$ pF (squares) and $C_2 = 8$ pF (circles). Contributions due to (a) I_B , (b) r_b , (c) I_c , and (d) R_L are shown; $f_0 = 946$ MHz and $\delta f = 25$ kHz. Ellipses group simulation and analytical curves (solid lines) for indicated values of C_2 .

where N_k refers to the spectral density of the k th noise source, $N_1 = 2qI_C$, $N_2 = 2qI_B$, $N_3 = 4kT/R_L$, and $N_4 = 4kTr_b$, and the subscript 0 indicates that only the contribution from the 0th harmonic at $f_0 - \delta f$ is calculated. Equations (3)–(7) predict the dependence of phase-noise contributions on circuit parameters such as circuit capacitors, bias currents, and parasitic resistors.

To test theoretical predictions, we compare noise contributions from the 0th harmonic calculated using (3)–(7) with those simulated with the nonlinear phase-noise simulator in SpectreRF in Fig. 4. The phase-noise spectral densities at 25-kHz offset from 946-MHz carrier are plotted as a function of capacitance C_3 for two different values of capacitor C_2 . Simulation results for $C_2 = 3.4$ pF and 8 pF are shown as solid squares and solid circles, respectively. Predictions of hand calculations are shown as solid lines in both cases. Results in Fig. 4 demonstrate good quantitative agreement between simulation and analytical results. The theoretical curves correctly capture trends in phase-noise variations and quantitatively lie within 30% error from simulated data.

IV. COMPARISON OF SIMULATIONS AND EXPERIMENT

To confirm the validity of nonlinear models implemented in a simulator, we compare results of simulations and measurements on a hard-driven Colpitts oscillator. The hard-driven case

represents the most challenging conditions under which one can test the performance of the simulator. A commercially available Colpitts oscillator circuit [12] was chosen for comparison purposes. Phase-noise simulations were performed with SpectreRF using measured device models and including all on-chip and off-chip parasitics. The frequency of oscillation is set at approximately 946 MHz, and the loaded Q of the off-chip resonator was close to 140. The single-sideband output noise spectrum of one of the production circuits was measured using the single-sweep power spectral density measurement on the spectrum analyzer. Measurement results shown in Fig. 5 indicate the total output noise power spectral density, which includes both AM- and PM-modulated components. Simulations with SpectreRF also compute the total output noise spectral density including both AM and PM components. Simulated and measured results are compared in Fig. 5 where we find a very good agreement between measurements and simulations. The flattening out of the phase noise with frequency in measured data at higher frequencies is due to noise in the buffer amplifier, which was not included in simulations.

V. CONCLUSION

In conclusion, we have presented an engineering approach to the analysis of phase noise in LC -tuned oscillators. The basic no-

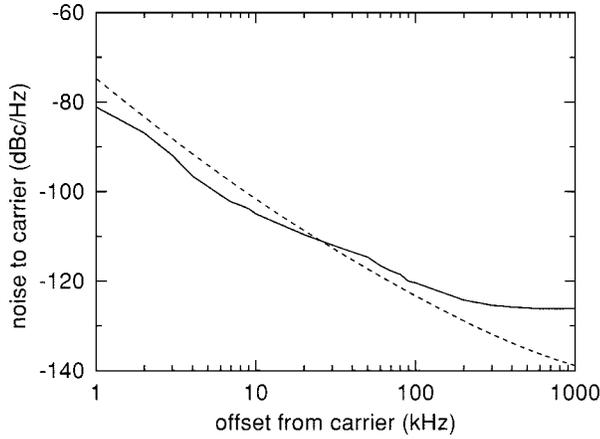


Fig. 5. Comparison of measurement (solid line) and simulation (dashed line) results for the practical Colpitts oscillator; offset is from 946-MHz carrier.

tion that has been explored in our theory is that an oscillator may be treated as a high-gain LC amplifier for phase-noise analysis. The techniques of oscillator noise analysis presented are intuitive and allow quantitative estimates of oscillator noise from circuit parameters. Theoretical predictions are in good agreement with nonlinear simulations using SpectreRF for weakly nonlinear oscillators. Validity of SpectreRF simulation models have been tested by comparing simulations and measurements under the most challenging conditions of a hard-driven oscillator, where we find that simulation and measurement results are in good agreement.

APPENDIX

For an oscillator operating in the steady state at a fundamental frequency f_0 , the nonlinear time-varying transconductance $g_m(t)$ can be represented by a sum over multiples of fundamental frequencies, as follows:

$$g_m(t) = \sum_{k=-\infty}^{+\infty} g_m^{(k)} e^{jk2\pi f_0 t} \quad (8)$$

where k is the number of the harmonic. From Kirchoff's equations at the collector of the active device, we obtain

$$g_m(t)v_1(t) = nv_1(t)/Z_T \quad (9)$$

where we assumed a linear transformer coupling with a transformation ratio 1 : n . Substituting (8) into (9) and summing current components at the fundamental frequency f_0 , we arrive at the oscillation condition

$$g_{m,\text{eff}} = g_m^{(0)} + g_m^{(2)} = \frac{n}{Z_T(f_0)}. \quad (10)$$

Next, we consider a noise source i_n at $f_0 - \delta f$ superimposed onto the oscillating waveform as shown in Fig. 1. The nonlinear transconductance $g_m(t)$ modulates this noise source to create noise sidebands at $f_0 - \delta f$ and $-f_0 - \delta f$ in the output waveform. At the input to the active device, we denote rms voltages of the former sideband by $v_1^{(+)}$ and of the latter by $v_1^{(-)}$. Similarly to

(9), we write Kirchoff's equations in the presence of the noise generator i_n for $f_0 - \delta f$ and $-f_0 - \delta f$ as

$$g_m^{(0)}v_1^{(+)} + g_m^{(2)}v_1^{(-)} + i_n = \frac{nv_1^{(+)}}{Z_T(f_0)} \quad (11)$$

and

$$g_m^{(0)}v_1^{(-)} + g_m^{(2)}v_1^{(+)} = \frac{nv_1^{(-)}}{Z_T(f_0)} \quad (12)$$

respectively. Solving for $v_1^{(+)} + v_1^{(-)}$ and $v_1^{(+)} - v_1^{(-)}$, we find

$$v_1^{(+)} + v_1^{(-)} = \frac{-i_n}{g_m^{(0)} + g_m^{(2)} - n/Z_T(f_0)} \quad (13)$$

and

$$v_1^{(+)} - v_1^{(-)} = \frac{-i_n}{g_m^{(0)} - g_m^{(2)} - n/Z_T(f_0)}. \quad (14)$$

Using the oscillation condition, (10), in (13) and (14), we find that in steady state the right-hand side of (13) peaks very sharply, and is much greater than the right hand side of (14). This leads to $v_1^{(+)} = v_1^{(-)}$, and to the expression for a single-sided transfer function, from i_n to $v_1^{(+)}$, given by

$$v_1^{(+)} = \frac{1}{2} \times \frac{-i_n}{g_{m,\text{eff}}^{(0)} - n/Z_T(f_0)}. \quad (15)$$

To obtain the output transfer function α_0 , we use $v_0^{(+)} = nv_1^{(+)}$ to arrive at

$$\alpha_0 = \frac{1}{2} \times \frac{R_L}{2jQ} \left(\frac{f_0}{\delta f} \right). \quad (16)$$

This is the noise transfer function from the noise tone at $f_0 - \delta f$ to the output noise of the oscillator at the same frequency. This transfer function explicitly contains a factor of 1/2, which is due to noise translation by $-2f_0$ to the negative frequencies at the output.

ACKNOWLEDGMENT

The authors would like to thank G. Mueller and B. Mack of Maxim Integrated Products, Inc., Sunnyvale, CA, for providing phase-noise measurement results.

REFERENCES

- [1] D. B. Leeson, "A simple model for oscillator noise spectrum," *Proc. IEEE*, vol. 54, pp. 329–330, Feb. 1966.
- [2] W. P. Robins, *Phase Noise in Signal Sources—Theory and Applications*. London, U.K.: Peregrinus, 1991.
- [3] J. Craninckx and M. Steyaert, "Low-noise voltage-controlled oscillators using enhanced LC -tanks," *IEEE Trans. Circuits Syst.—II*, vol. 42, pp. 794–804, Dec. 1995.
- [4] B. Razavi, "A study of phase noise in CMOS oscillators," *IEEE J. Solid-State Circuits*, vol. 31, pp. 331–343, Mar. 1996.
- [5] H. Siweris and B. Schieck, "Analysis of noise upconversion in microwave FET oscillators," *IEEE Trans. Microwave Theory Tech.*, vol. MTT-33, pp. 233–241, Jan. 1985.
- [6] C. Samori, A. L. Lacaita, F. Villa, and F. Zappa, "Spectrum folding and phase noise in LC tuned oscillators," *IEEE Trans. Circuits Syst.—II*, vol. 45, pp. 781–789, July 1998.
- [7] F. Kaertner, "Analysis of white and $f^{-\alpha}$ noise in oscillators," *Int. J. Circuits Theory Appl.*, vol. 18, pp. 485–519, 1990.
- [8] A. Demir, "Analysis and Simulation of Noise in Nonlinear Electronic Circuits and Systems," Ph.D. dissertation, Univ. of California, Berkeley, CA, 1997.

- [9] A. Hajimiri and T. H. Lee, "A general theory of phase noise in electrical oscillators," *IEEE J. Solid-State Circuits*, vol. 33, pp. 179–194, Feb. 1998.
- [10] Oscillator Noise Analysis in SpectreRF: Cadence Design Systems, Inc., to be published.
- [11] K. K. Clarke and D. T. Hess, *Communication Circuits: Analysis and Design*. Redding, MA: Addison-Wesley, 1971, ch. 6.
- [12] "10 MHz to 1050 MHz Integrated RF Oscillator with Buffered Outputs, Maxim Wireless Analog Design Solutions Guide," Maxim Integrated Products, Inc., Sunnyvale, CA, 1999.